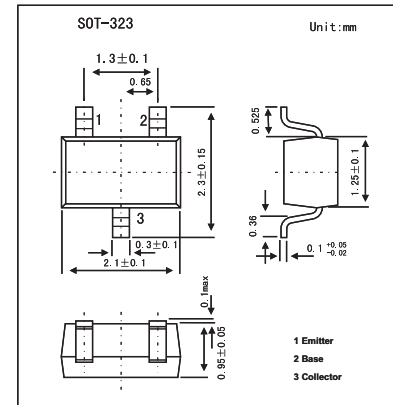


PNP General Purpose Transistors

KC860W(BC860W)

■ Features

- Low current (max. 100 mA)
- Low voltage (max. 45 V).

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-Base Voltage	V_{CB0}	-50	V
Collector-Emitter Voltage	V_{CE0}	-45	V
Emitter-Base Voltage	V_{EB0}	-5	V
Collector Current DC	I_C	-100	mA
Peak collector current	I_{CM}	-200	mA
Peak base current	I_{BM}	-200	mA
Power Dissipation	P_D	200	mW
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	625	K/W
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-65 to +150	$^\circ\text{C}$

KC860W(BC860W)■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-Cutoff Current	I _{CBO}	V _{CB} = -30 V, I _E = 0			-15	nA
		V _{CB} = -30 V, I _E = 0, T _A = 150°C			-4	μA
Emitter- cutoff current	I _{EBO}	I _C =0, V _{EB} =-5V			-100	nA
DC Current Gain	KC860W	I _C = -2.0 mA, V _{CE} = -5.0 V	220		800	
	KC860BW		220		475	
	KC860CW		420		800	
Collector-Emitter Saturation Voltage	V _{CE(sat)}	I _C = -10 mA, I _B = -0.5 mA			-300	mV
		I _C = -100 mA, I _B = -5.0 mA			-650	mV
Base-Emitter Voltage	V _{BE}	I _C = -2mA, I _B =-5A	-600		-750	mV
		I _C = -10 mA, I _B =-5A			-820	mV
Collector capacitance	C _c	I _E = i _e = 0; V _{CB} = -10 V; f = 1 MHz			5	pF
Emitter capacitance	C _e	I _C = i _c = 0; V _{EB} = -500 mV; f = 1 MHz		10		pF
Noise figure	F	I _C = -200 μA; V _{CE} = -5 V; R _S = 2 kΩ; f = 10 Hz to 15.7 kHz			4	dB
		I _C = -200 μA; V _{CE} = -5 V; R _S = 2 kΩ; f = 1 kHz; B = 200 Hz			4	dB
Transition frequency	f _T	I _C = -10 mA; V _{CE} = -5 V; f = 100 MHz	100			MHz

■ Marking

NO.	KC860W	KC860BW	KC860CW
Marking	4H	4F	4G